KRAVCHENKO, A.A., kand.med.nauk

Therapeutic use of radicactive phosphorus in osteoplastic surgery; experimental studies. Ortop.travm. i protez. 20 no.6:79-83 Je '59.

(MIRA 13:3)

1. Iz Ukrainskogo nauchno-issledovatel skogo instituta ortopedii i travmatologii im. M.I. Sitenko (direktor - chlen-korrespondent AMN SSSR prof. N.P. Novachenko).

(PHOSPHORUS, radicactive, eff. on bone regen. after exper. osteoplasty (Rus))

(BONE AND BONES, surg.

porop. bone regen. (Rus))

exper. osteoplasty, eff. of radiophsophorus on

KRAVCHENKO, A.A., kand.med.nauk (Khar'kov, Degtyarnaya ul., 14, kv.48).

Clinical evaluation of osteoplastic operations in the treatment of recent and unknitted fractures of the long bones. Vest. khir. 83 no.7:62-69 Jl '59. (MIRA 12:11)

1. Iz Ukrainskogo nauchno-issledovatel'skogo instituta ortopedii i travmatologii im. prof.M.I.Sitenko (dir. - prof.N.F.Novachenko). (BOHE GRAFTING)

KRAVCHEKO, A.A., kand.med.nauk

Biological effect of radioactive phosphorus on the osteogenic capacity of an injured osseous organ. Trudy Ukr. nauch.-issl. inst. ortop. i travm. no.15:347-354 '59. (Mira 16:12)

l. Iz Ukrainskogo nauchno-issledovatel'skogo instituta ortopedii i travmatologii imeni prof. M.I.Sitenka (dir.-chlenkorrespondent AMN SSSR prof. N.P.Novachenko).

KRAVCHENKO, A. A.

Inhalation effect of the water of Hot Springs, No. 63 on blood pressure in hypertension. Sovet. med. no.8:32-34 Aug. 1950.

(CIML 20:1)
1. Of the Clinic for Ear, Throat, and Nose Diseases (Director -- Prof. V. K. Suprunov), Kuban' Medical Institute imeni Krasnaya Armiya.

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

Metastases of ovarial tumor simulating thrombosis of the cavernous sinus. Vest.oto-rin. 18 no.5:115-116 S-0 '56. (MLRA 9:11)

1. Iz kliniki bolesney ukha, gorla i nosa Moskovskogo oblastnogo klinicheskogo instituta (dir. - prof. I.Ya. Sendul'skiy)

(OVARIES, neoplasms

metastases to cavernous sinus simulating thrombosis)

(VEINS, CRANIAL SINUSES, neoplasms

metastatic from ovaries in cavernous sinus simulating thrombosis)

(THROMBOSIS, differ. diag.

cavernous sinus therombosis simulated by metastatic tumor from ovaries)

KRAVCHENKO, A.A., starshiy nauchnyy sotrudnik

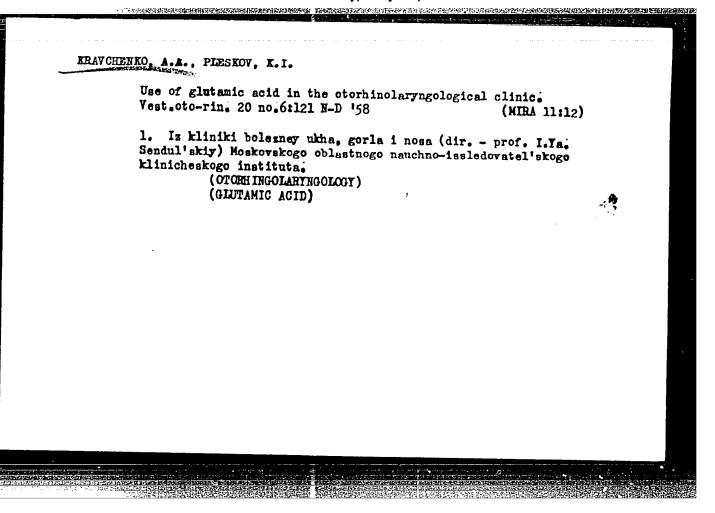
Exacerbation of chronic suppurative epitympanitis of the left ear in Addison's disease. Vest. oto-rin. 19 no.1:99-100 Ja-7 '57

(HIRA 10:4)

1. Is kliniki bolezuey ukha, gorla i nosa (dir.-prof. I.Ya. Sendul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta.

(KAR, MIDDLE, diseases, epitympanitis, exacerbation in Addison's dis.) (Rus)

(ADDISON'S DISKASE, complications, epitympanitis, exacerbation) (Rus)



SVETLAKOV, M.I., dotsent, KRAVCHENKO, A.A., kand.med.nsuk, PLESKOV, K.I.

Use of hemopoietic stimulators in radiotherapy for cancer of the larynx. Vrach.delo no.5:527 My '58 (MIRA 11:7)

1. Klinika bolezney ukha, gorla i nosa (zav. - prof. I.Ya. Sendul' skiy) Moskovskogo oblastnogo nsuchno-issledovatel'skogo klinicheskogo instituta i TSentrel'nogo instituta usovershenstvovaniya vrachay.

(IARYEN-CANCER)

(IMUCOPENIA)

(X RAYS-PHYSIOLOICAL FFFECT)

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SVETLAKOV, M.I., polkovník med.sluzhby, dots.; KRAVCHENKO, A.A., kand.med.

Nasal and pharyugeal hemorrhage requiring hospital therapy. Voen.-
med.zhur. no.12:60-62 D '58.

(MPISTAXIS, ther.
severe, in hosp. (Rus))

(PHARYNX, hemorrh.
ther., in hosp. (Rus))
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SVETIAKOV, M.I., dots.; KHAVCHENKO, A.A., kand.med.nauk

Tympanoplasty in chronic suppurative otitis media. Vest.otorin.
20 no.2:20-23 Mr-Ap '58. (MIRA 12:11)

1. Iz kliniki bolezney ukha, gorla i nosa (zav. - prof.I.Ya.
Sendul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo
klinicheskogo instituta i TSentral'nogo instituta usovershenstvovaniya vrachey.

(OTITIS MEDIA, surg.

tympanoplasty in chronic suppurative dis.

(Hus))

SVETLAKOV, M.I.; KRAVCHENKO, A.A.; KARPUKHIN, V.I.

DE LA LEGIO DE LA CONTRACTOR DE LA CONTR

Changes in arterial pressure in patients with laryngeal cancer in operations on the neck under potentiated local anesthesia. Akt. vop. obezbol. no.2:182-194 (59. (MIRA 14:5)

1. Iz kliniki bolezney ukha, gorla i nosa (zaveduyushchiy - pref. I.Ya.Sendul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta i TSentral'noy klinicheskoy bol'nitsy Ministerstva putey soobshcheyina (nanchnyy rukovoditel' - prof. Ministersus T.P.Makarenko) (BLOOD PRESSURE)

(LARYNX -- CANCER) (LOCAL ANESTHESIA)

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MHAVCHENKO, A.A.; PASTERNAK, A.Ye.; LARCHENKO, R.M.; SOKOLOVA, L.I.

Diseases of the upper respiratory tract and ears in workers at the Serpukhov textile mills. Gig. i san. 24 no.6:48-51 Ja '59. (MIRA 12:8)

1. Iz Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo, Moskovskogo nauchno-issledovatel'skogo instituta sanitarii i giglyeny imeni F.F.Zriemana i ob"yedinennoy bol'nitsy imeni Semashko Serpukhova. (OCCUPATIONAL DISMASS ear & upper resp. tract dis. in textile workers (Rus)) (RAR, dis. occup., in textile workers (Rus)) (RESPIRATORY TRACT, dis. same)
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KRAVCHENKO, A.A.; NEVRAYEVA, A.S.

Autonomic labyrinthine reactions in patients with hypertension treated by inhalation of artificial hydrogen sulfide water (outside of a health resort). Terap.arkh. 31 no.10:33-37 0 159.

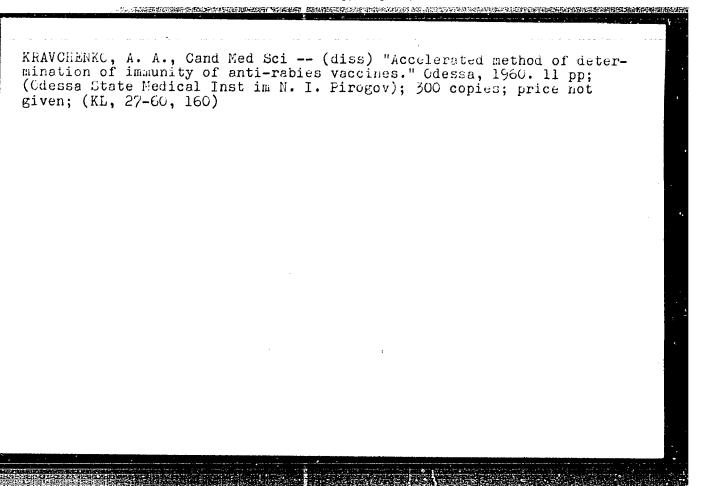
(MIRA 13:3)

1. Iz TSentral'nogo instituta kurortologii (direktor G.N. Pospelova)

i kliniki ushnykh, gorlovykh i nosovykh bolezney (direktor - prof.

I.Ya. Sendul'skiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni M.F. Vladimirskogo.

(MINERAL WATER, ther.)
(HIPERTENSION ther.)
(SULFIDES ther.)



KRAVCHENKO, A.A. (Moskva); PASTERNAK, A.Ye. (Moskva); NARYSHKINA, T.F. (Moskva) Vol'FSON, M.T. (Moskva)

Occupational pathology of the otolaryngological organs in workers of cotton mills. Gig. truda i prof. zab. 4 no.6:41-43 Je '60. (MIRA 15:4)

1. Moskovskiy oblastnoy klinichoskiy institut imeni M.F. Vladimirskogo, Institut sanitarii i giglyeny imeni F.F. Erismana i Bol'nitsa fabriki "Krasnyy tekatil'shohik". (COTTON MANUFACTURE--HYGIENIC ASPECTS) (OTOLARYNGOLOGY)

Influence of inhalations of artificial hydrogen sulfide wiater on the oscillographic indexes of hypertension patients. Vrach. delo no.7:117-119 J1 '60. (MIRA 13:7)

1. TSentral'nyy institut kurortologii i klinika ushnykh, gorlovykh i nosovykh bolesney Moskovskogo oblastnogo nauchno-issledovatel'-skogo klinicheskogo instituta.

(HYDROGEN SULFIDE) (HYPERTENSION)

KHAVCHENKO, A.A.; GORBACHEVA, K.M.; BOGOMOLOVA, Ye.R.; BITSADZE, L.R.

Change in the auditory function of the ear in treating hypertension with some medicinal substances (preliminary report). Vop. klin. pat. no.3:78-88 '61. (Min 14:12)

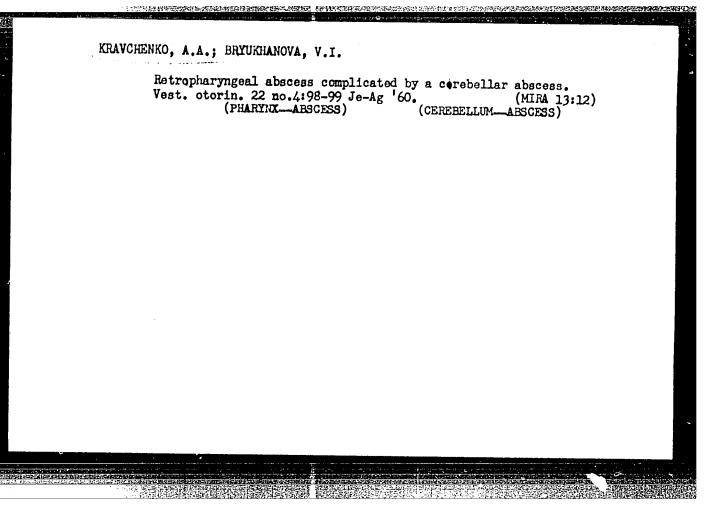
l. Iz Kliniki bolezhey ukho, gorla i nosa (zaveduyushchiy zasluzhennyy deyatel' nauki prof. I.Ya.Sendul'akiy) Moskovskogo oblastnogo nauchno-issledovatel'skogo instituta imeni M.V.Vladimirskogo.

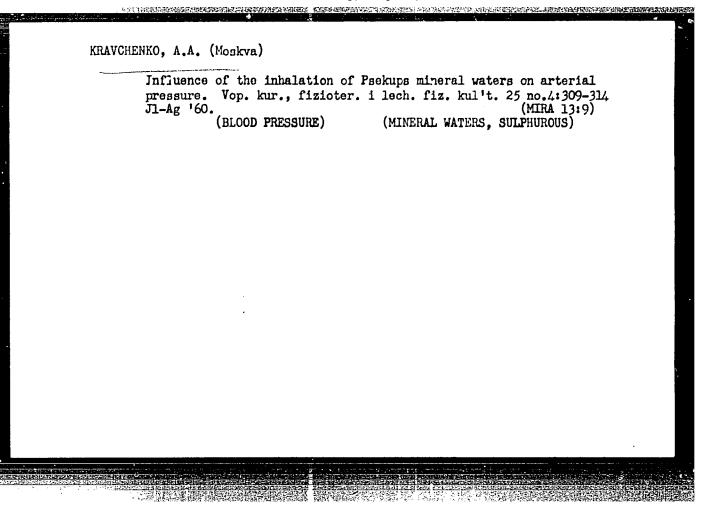
(HYPERTENSION) (HEARING)

REAVCHENKO, A.A.; BOGOMOLOVA, Ye.R.; PLESKOV, K.I.; YUDIN, Yu.O.

Problem of clinical and morphological changes of the upper respiratory tract and ear in leukoses. Vest. otorin. 22 no. 4:33-38 Je-Ag '60. (MIRA 13:12)

(RESPIRATORY ORGANS) (EAR) (LEUKEMIA)





KRAVCHENKC, A.A.: NEVRAYEVA, A.S.

Condition of the auditory analysor in hypertension patients treated with vapor inhalations from hydrogen sulfide water. Vop. kur., fizioter. i lech. fiz. kul't. 26 no.5:420-426 S-0 '61. (MTR 14:11)

TENNING TO THE PROPERTY OF THE

l. Iv TSentral'nogo instituta kurortologii (dir. G.N.Pospelova) i kliniki ushnykh, gorlovykh i nosovykh bolezney (dir. - prof. I.Ya. Sendul'skiy), Moskovskogo oblastnogo klinicheskogo instituta (dir. P.M.Leonenko, rukovoditel' raboty-prof. Z.Ye.Bykhovskiy).

(HYPERTENSION) (MINERAL WATER, SULFUROUS)

(ACOUSTIC MERVE)

KRAVCHENKO, A.A., starshiy nauchayy sotrudnik; MIRONOV, B.I.;

EALASHOV, V.I.

Vestibulometry and qxyhemometry in hypertensives. Trudy
MONIKI np.5:115-131 '62' (MIRA 16:4)

1. Otorinolaringologicheskaya klinika Moskovskogo oblastnogo
nauchno-issledovatel skogo kliniches.ogo instituta (direktor zasluzhennyy doyatel 'naukt, prof. I.Ya.Sendul'skty.

(HYPERTENSION) (VESTIEULAR APPARATUS)

(BLOOD—OXYGEN CONTENT)

KRAVCHENKO A.A. starshiy nauchnyy sotrudnik

Some data concerning the effect of sulfide mineral water on the brain blood vessels and the pressure of the cerebrospinal fluid. Trudy MONIKI no.5:142-159 *62. (MIRA 16:4)

1. Otorinolaringologicheskaya klinika Moskovskogo oblastnego nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo (dir. zasluzhennyy deyatel' nauki, prof. 1.Ya. Sendul'skiy) i laboratoriya eksperimental'noy patofiziologii mozga Instituta nevrologii AMN SSSR (zav. chlen-korrespondent AMN SSSR B.N.Klosovskiy).

(MINERAL WATER, SULFUROUS) (HRAIN-BLOOD SUPPLY)
(CEREBROSPINAL FLUID)

KRAVCHENKO, A.A., starshiy nauchnyy sotrudnik

Late results of treatment of hypertension patients with auditory and vestibular disorders by means of sulfide water inhalations. Trudy MONIKI no.5:160-176 '62. (MIRA 16:4)

1. Klinika ushnykh, gorlovykh i nosovykh bolezney Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo (dir. - zasluzhennyy deyatel' nauki, prof. I.Ya.Sendul'skiy).

(HYPERTENSION) (EAR-DISEASES) (INHALATION THERAPT)

KRAVCHENKO, A.A., starshiy nauchnyy sotrudnik

State of the auditory analyser in hypertension patients treated by inhalation of natural sulfide water. Trudy MONIKI no.5:177-206 '62. (MIRA 1614)

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1. Klinika ushnykh, gorlovykh i nosovykh bolezney Moskovskogo oblastnogo nauchno-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo (dir. - zasluzhennyy deyatel' mauki, prof. I.Ya.Sendul'skiy).

(HYPERTENSION) (EAR-DISEASES) (INHALATION THERAPY)

KRAVCHENKO, A.A.; BOGOMOLOVA, Ye.R.; PLESKOV, K.I.; YUDIN, Yu.G.

Glinical and morphological changes in the ear, nose and throat in reticulosis with a tumorlike growth. Vop. klin. pat. no.2:244-251 *61 (MIRA 16:12)

1. Iz kliniki bolezney ukha, gorla i nosa (zav. - sasluzhennyy deyatel' nauki prof. I.Ya. Sendul'skiy) i patomorfologicheskogo otdela (zav. - prof. S.B. Vaynberg [deceased]) Moskovskogo oblastnogo nauchne-issledovatel'skogo klinicheskogo instituta imeni Vladimirskogo.

ARUTYUNOV, V.Ya., prof.; KRAVCHENKO, A.A., doktor med. nauk; CHINCKOVA, V.A., kand. med. nauk Wegener's syndrome. Vest. derm. 1 mm. 32 no.5:30-35 My 163. (MIRA 17:5)

1. Klinika kozhnykh i venerieleskh bolezney (dir. - ref. V.Ya. Arutyunov) otolaringologichaskaya klinika (dir. - zasluzhannyy deyatel' nauki prof. I. Ya. Sendul'skiy) i patomerfologicheskiy otdel (zav. - chlen-korrespondent AMN SSSR prot. 1. P. Avtsyn) Moskovskogo oblastnogo nauchno-issledovatel sko o klimicheskogo instituta imeni M.F. Vladimirskogo (dir. - zasluzuemnyy vrach P.M. Leonenko).

DOROFEYEV, V.G.; KITOV, A.N.; KRAVCHENKO, A.A., inzh., retsenzent; HRAYLOVSKIY, N.G., inzh., red.; KHITROVA, N.A., tekhn.red.

[Servicing of passenger cars] Ekipirovka passazhirskikh vagonov. Moskva, Izd-vo "Transport," 1964. 135 p. (MIRA 17:3)

ENT(1)/EEC(b)-2/EAD-2 IJP(c)/AS(mp)-2/AFTC(b)/SSD/AFWI/ASD(a)-5/ L 12021-65 5/0302/64/000/003/0062/0064 RAEM(c)/ESD(t) ACCESSION NR: AP4046115

AUTHOR: Kravchenko, A. A.

TITLE: Instrument for determining local values of magnetic field strength along the symmetry axis of magnetostatic lenses of an electron microscope

SOURCE: Avtomatika i priborostroyeniye, no. 3, 1964, 62-64

TOPIC TAGS: electron microscope, magnetic field strength, magnetic field, magnetostatic lens

ABSTRACT: The instrument consists of a Hall-generator-type sensor made from a Ge single crystal, a microammeter, and auxiliary switches and resistors. The sensor can be placed by a micrometer screw to any position on the magnetic lens axis. The instrument characteristics are: ranges, 0-100, 0-500, 0-1,000, 0-5,000, 0-10,000, 0-15,000 gs: basic error, \$2%; sensitivity, 40 microvolt/oe; sensor size, 2.5x2.5x0.3 mm. Orig. art. has: Z figures and 1 table.

Card 1/2

CIA-RDP86-00513R000826230(APPROVED FOR RELEASE: Monday, July 31, 2000

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Card 2/2						

OVECHKIS, YE. S., KRAYCHENKO, A. D., GRAD, N. YE. IRLINOKIY, D. A., TSIFENYUK, A. YA.

Hides and Skins

Efficient method for measuring stiff hides. Leg. prom. 12 no. 8, 1952.

Fonthly List of Russian Accessions. Library of Congress, October 1952. UNCLASSIFIED.

KRAVCHENKO, A.D., inzh.

Semiautomatic machines for shaping and assembling shoes having sewed and glued soles. Izv. vys. ucheb.zav.; tekh.leg. prom. no.1:57-66 '58. (MIRA 11:6)

1. Ukrainskiy nauchne-issledovatel'skiy institut kozhevenne-obuvnoy promyshlennosti.

(Shee machinery)

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

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KRAVCHENKO, A.D., inzh.

Using the method of two-dimensional stretching in investigating physical and mechanical properties of chrome-tanned calf leather. Izv.vys.ucheb.zav.; tekh.leg.prom. no.4:45-58 '58. (MIRA 11:12)

l. Ukrainskiy nauchno-issledovatel'skiy institut kozhevennoobuvnoy promyshlennosti. (Leather--Testing)

THE CONTROL OF STREET AND STREET STREET, STREET STREET, STREET STREET, STREET, STREET, STREET, STREET, STREET,

KRAVCHENKO, A.D., inzh.

Investigating physicomechanical properties of chrome-tanned calfskin by two-dimensional stretching. Izv.vys.ucheb.zav.; tekh.leg.prom. no.5:35-46 158. (MIRA 12:2)

1. Ukrainskiy nauchno-issledovatel'skiy institut kozhevenno-obuvnoy promyshlennisti.

(Leather -- Testing)

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

ACTURE DANGERS COMPARED BY THE PROPERTY OF THE

KRAVCHENKO, A.D., inzh.; Prinimala uchastiye: ROKHLENKO, R.

Studying the effect of moisture on the deformation of shoe upper materials in cases of two-dimensional stretching. Izv.vys.ucheb. zav.; tekh.leg.prom. no.6:84-91 '61. (MTRA 14:12)

1. Ukrainskiy nauchno-issledovatel skiy institut kozhevenno-obuvnoy promyshlennosti. Řekomendovana kafedroy tekhnologii obuvnogo proizvodstva Kiyevskogo tekhnologicheskogo instituta legkoy promyshlennosti.

(Shoe manufacture)
(Strains and stresses)

KRAVCHENKO, A.D., inzh.

Investigating the deformation of shoe uppers and their fastening to the sole parts on a semiautomatic multiple-operation line for the forming and assembly of welt footwear. Nauch.-issl.trudy Ukr

NIIKP no.13:117-131 '62. (MIRA 18

26.2421

26028

S/.39/61/000/003/008/013 E036/E335

AUTHOR:

Kravchenko, A.F.

TITLE:

Some Electrophysical Properties of Gallium

Arsenide

PERIODICAL: Izvestiya vysshikh uchebnykh zavedeniy,

Fizika, 1961, No. 3, pp. 80-87

TEXT: An account is given of the investigation of the temperature dependence of the electrical conductivity, thermo-electric e.m.f. and the Fermi level in gallium arsenide of both conductivity types. The effective masses and concentrations of electrons and holes and the variation of the Hall coefficient with both temperature and magnetic field were determined and thus also the temperature dependence of the mobility. These experimental results are compared with theoretical calculations and some comments are made on the carrier scattering mechanism. The author states that insufficient work of this sort has been carried out to make possible some conclusions on the energy structure or conduction mechanism of gallium arsenide. Rectangular parallelopiped Card 1/6

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26028 S/139/61/000/003/008/013
Some Electrophysical Properties ... E036/E335

samples were cut from polycrystalline ingots, the surface was then ground and the surface layer, which was deformed by cutting and grinding, removed by etching. Then, narrow strips of silver were deposited on the sides of the samples and tungsten probes pressed onto these for the Hall measurements and for the conductivity determination by a compensation method. Direct current was used for the Hall measurements. The usual compensation technique was used to measure the thermo-electric e.m.f. to an accuracy of \pm 1 μV . The temperature difference along the sample of 10 - 15 $^{\circ}$ C was measured with two copperconstantan thermocouples. The differential thermo-e.m.f. was measured with respect to the copper branch of the thermocouple. In some cases the samples cut comprised a single crystal and no significant difference was observed between these samples and those containing two or three crystals. The measured thermoelectrical e.m.f. are of the order 0.03 - 0.05 mV/deg for n-type and 0.1 - 0.2 mV/deg for p-type material at room temperature. These values increase for both types with increasing temperature. Measurements are plotted over the range 300 K to approximately 600 K. The conductivity of n-type material increases slowly Card 2/6

26028 S/139/61/000/003/008/013 Some Electrophysical Properties E036/E335

with temperature to reach a maximum at 423 $^{\circ}\mathrm{K}$ and then decreases. At about 473 $^{\circ}\mathrm{K}$ the conductivity again sharply increases. In some n-type samples the conductivity is almost independent of temperature up to $473\,^{\circ}\mathrm{K}$ and then slowly increases. The conductivity of p-type material increases from room temperature somewhat more rapidly than that of natype. The Hall constant of netype is independent of temperature from low temperatures up to \$\sigma 200 \text{ K}\$. A slight decrease of the Hall constant is observed for p-type material over this range. This change is stated to be less than that reported by Folberth and Weiss (Ref. 4 - Z. Baturforsch, 10a. 615, 1955). Over this range the conductivity of both no and p-type samples increased. The variation of the Hall constant with the magnetic field was measured at room temperature. For n-type samples a slight linear decrease with the field was observed. The decrease was smaller for the larger carrier concentrations and in one case was independent of the field over the range 80 to 20 000 Oe. The Hall constant of p-type samples drops sharply as the field is increased from 80 to 4 000 0e. From 6 000 0e it is practically constant. After this investigation all Hall Card 3/6

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26028 S/139/61/000/003/008/013 Some Electrophysical Properties E036/E335

measurements were carried out above 6 000 0e. The temperature dependence of the carrier mobility calculated from these Hall and conductivity measurements showed an increase from room temperature to a maximum at 400-420 K for n-type and at about 500 K for patype. The typical mobilities were about $200 - 300 \text{ cm}^2/\text{Vsec}$ and 1 $400 - 1600 \text{ cm}^2/\text{Vsec}$ for p- and ntype samples, respectively. The author states that measurements of the Nernst-Ettingshausen effect on these samples indicated that at lower temperatures scattering by impurities was dominant. This work is to be discussed in a separate paper. The decrease of mobility at the higher temperature and the slight dependence of the Hall constant on temperature suggests that the samples are degenerate. Variations of the Hall constant of Ge and InSb with magnetic field similar to those reported here have been explained by the presence of light and heavy holes and this may be the explanation in the case of gallium arsenide. The position of the Fermi level is calculated from the thermo-electric e.m.f. and supports the conclusions that the samples are degenerate. Card 4/6

26028 S/139/61/000/003/008/013 Some Electrophysical Properties ... E036/E335

The carrier concentrations at room temperatures are calculated from Hall data to be $\sim 4.5 \times 10^{17} \text{cm}^{-3}$ for netype and $\sim 7.8 \times 10^{17} \text{cm}^{-3}$ for p-type and the variation with temperature tallies with the degeneracy. The effective masses calculated from the data are 0.024 $\rm m_{_{O}}$ for electrons and 0.093 $\rm m_{_{O}}$ for holes, where $\rm m_{_{O}}$ is the free electron mass. The observed thermo-electric $e \circ m \circ f \cdot is$ are somewhat less than those calculated on the basis of one carrier type and may be due to the presence of carriers of both signs. Summarising, the increasing natype conductivity is consistent with impurity scattering, whilst with p-type the number of carriers also increases. The decrease in mobility at higher temperatures is due to thermal scattering. The fact that the maximum conductivity is observed at a higher temperature in p-type than in n-type is explained by the higher carrier concentration in p-type samples. The abrupt increase of netype conductivity at high temperatures could be due to deep impurity levels. The author expresses his gratitude to Card 5/6

26028 S/139/61/000/003/008/013 Some Electrophysical Properties ... E036/E335

CONSISTENCIA DE LA CONTROL DE

V.A. Presnov for the samples and to A.F. Gorodetskiy for interest in the work. There are 9 figures and 13 references: 6 Soviet and 7 non-Soviet. The four English language references quoted are: Ref. 2 - H. Welker - J. Electronics: 1: 181, 1955; Ref. 3 - R. Barrie, F. Cunnell J. Edmond. J. Ross - Physica, 20, 11, 1087-1090, 1954, Ref. 11 - R. Willardson, T. Harman, A. Beer - Phys. Rev. 96, 1512, 1954; Ref. 12 - J. Tauc - Phys. Rev., 95, 1394, 1954.

ASSOCIATION: Novosibirskiy elektrotekhnicheskiy institut

(Novosibirsk Electrotechnical Institute)

SUBMITTED: May 9, 1960 (initially)

November 26, 1960 (after revision)

Card 6/6

KRAVCHENKO, A.F.; FEN, G.Yu.

Galvanomegnetic and thermomagnetic phenomena in n-type Gals.
Fig. tver. tela 1.no.2:660-666 F '63. (MIRA 16:5)

1. Novosibirskiy elektrotekhnicheskiy institut.
(Thermomagnetism) (Thermoelectricity) (Gallium arsenide)

L 35490-65 EWT(1)/EWT(m)/EWP(w)/EWA(d)/T/EWP(t)/EWP(h)/EWA(h) Pz-6/Peb ACCESSION NR: AP5007839 [(c)] JD/RT S/0288/64/000/003/0091/0095

AUTHOR: Kravchenko, A.F.; Kot, K.N.; Divak, M.I.

TITLE: Microhardness of gallium arsenide

SOURCE: AN SSSR. Shirskoye otdeleniye. Izvestiya. Seriya tekhnicheskikh nauk, no. 3, 1964, 91-95

TOPIC TAGS: gallium arsenide, gallium arsenide hardness, single crystal hardness, microscope hardness, semiconductor hardness, semiconductor crystal structure

ABSTRACT: Only a few papers deal with the microstructure of GaAs (see e.g., G.A. Wolft, L. Toman, F.I. Field, J.C. Clavk, Somiconductors and Phosphors, New Jersey, 1958 for polycrystalline samples). The present paper reports on measurements of the microhardness of oriented monocrystals having a free electron concentration of n 2 1017 cm 3, and a dislocation density in the (111) plane between 2-104 and 5-105 cm 2. Samples were polished by etching (1 part HF, 3 parts HNO₃, and 2 parts H₂). The microhardness in the [111] plane is H = 650 kg/mm²; in [110] - 510 kg/mm². Annealing at temperatures not higher than 400C increases the microhardness, which also depends on the orientation of the indenter with respect to the crystallographic directions

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	THE REPORT OF THE PROPERTY OF	
ACCESSION NR: AP5007839 and is determined by the distribution ality between the microhardness	oution and mobility of dislocations. There is a proportional and the heat of formation of AIIBV. The viscosity of the case and the heat of formation. Orig. art. has: 2 formulas,	
samples with in the fifth plane		29
Solid State Physics and Semicon	verdogo tela i poluprovodnikovov, elektroniki, (<u>Institute for ductor Electronics</u>)	
SUBMITTED: 10Jan64	ENCL: 00 SUB CODE: SS, EC	
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Refrence and France Company of the C Pt-10 IJP(c)/APML/SSD/ ENT(1)/EPA(c)-2/ENT(m)/ENP(t)/ENP(b) AS(mp)-2/ASD(a)-5/RAEM(a)/ESD(gs)/ESD(t) JD s/0139/64/000/005/0062/0068 ACCESSION NR: AP4047349 AUTHOR: Kravchenko, A. F. Magnetoresistance in n-type gallium arsenide TITLE: IVUZ. Fizika, no. 5, 1964, 62-68 SOURCE: TOPIC TAGS: gallium arsenide, magnetoresistance, galvanomagnetic effect, conduction band, carrier density, Hall effect ABSTRACT: The purpose of this investigation was to study further the structure of the conduction band in n-type GaAs and to obtain additional information concerning the location and form of the additional minima of the conduction band (in excess of those in germani-The tests were made over a wide interval of temperatures and concentrations, and in different crystallographic directions. The samples were in the form of right parallelepipeds 0.1 x 0.3 x 1.0 Much attention was paid to the surface finish and to the quality Card

L 11967-65

ACCESSION NR: AP4047349

of the current contacts. The temperature range was 4.2--300K, and the free-garrier density, calculated from the Hall effect, was 104 cm⁻³--10¹⁸ cm⁻³ at room temperature. The results have shown that the constant-energy surface is anisotropic in K-space for samples with carrier density <107 cm-3. There is practically no anisotropy when the impurity content is high. The coefficients of the magnetoresistance tensor were calculated for samples with different impurity concentration and different temperatures. The relation between these coefficients shows that the conduction of these samples lies in the lowest conduction band which has many minima distributed along the [100] axis. In these minima, the equal-energy surfaces are ellipsolds of revolution with major axes along the [100] direction. anisotropy exponent of the minima on [100] is close to the analogous anisotropy exponent or the minima on [200, 200], and minima for silicon. At liquid helium temperature, a negative magnitude with density $n \sim 10^{17}$ cm⁻³; neto-resistance is observed for samples with density $n \sim 10^{17}$ cm⁻³ this magnetoresistance is isotropic. Several hypotheses are advanced concerning the structure of the conduction bands of GaAs.

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elektrotekhnicheskiy ir	stitut (Novo-
1802.400	encl: 00
NR REF SOV: 003	OTHER: 021
	4 figures, 8 formulas, 4 elektrotekhnicheskiy in 1 natitute)

Whateness, A.F.; MOSHKIN, L.N.

Unit for measuring the lifetime of minority charge carriers in semiconductors. Zov. Inb. 31 no.1: 26-127 '65.

(MIRA 18:3)

1. Novosibirskiy elektrotekhnichsokiy institut.

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L 2551-66 EWT(m)/EWP(w)/EPF(c)/EWP(j)/T/EWP(t)/EWP(b) IJP(c) JD/RM
ACCESSION NR: AP5021083	UR/0288/65/000/002/0153/0154 537.311.33 -44
AUTHOR: Kornilovich, A. A.; Kravchenko, A. F.	4/
TITLE: Effect of heat treatment on the electric phosphorus as an impurity	
SOURCE: AN SSSR. Sibirskoye otdeleniye. Izver no. 2, 1965, 153-154	stiya. Seriya tekhnicheskikh nauk,
TOPIC TAGS: high temperature annealing, low tensilicon, phosphorus impurity, free electron mobit trical resistance, electroneutral silicon dioxid	llity. donor concentration, elec-
ABSTRACT: Heating of Si to temperatures above properties; the reason for this is not conclusive ries on the interaction of oxygen with atoms of been advanced. In this connection, the authors	rely known, although certain theo- silicon and atoms of impurities have present the results of an experi-
mental investigation of electrical resistance, obility as a function of the time and temperature of three groups of n-Si containing different amowas performed in a vacuum (10 ⁻³ mm Hg) at from 4 and the cooling, for 10 hr, inside the furnace.	on the heat treatment (annualing) ounts of P impurity. The annualing
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depending on the temperature range in which it was performed: above 800C the Hall coefficient and free-electron mobility tended to increase (most sharply in the material with the lowest content of P), while electrical resistance remained constant; below 800C (low-temperature annealing) the Hall coefficient and the electrical resistance of Si decreased while electron mobility somewhat increased. Annealing beyond 30 min no longer affected the electrical characteristics and parameters of Si. The differences in the effect of heat treatment on electrical properties are conditioned by the presence of oxygen in silicon in the form of monodisperse Si ₂ O groups. In the process of the heating of Si to 1000C the oxygen atoms become regrouped Si ₂ O + SiO ₂ + Si The electrically neutral groups of SiO ₂ interact with the phosphorus 5SiO ₂ + 4P - 2P ₂ O ₅ + 5Si	
coefficient and free-electron mobility tended to increase (most sharply in the material with the lowest content of P), while electrical resistance remained constant; below 800C (low-temperature annealing) the Hall coefficient and the electrical resistance of Si decreased while electron mobility somewhat increased. Annealing beyond 30 min no longer affected the electrical characteristics and parameters of Si. The differences in the effect of heat treatment on electrical properties are conditioned by the presence of oxygen in silicon in the form of monodisperse Si ₂ O groups. In the process of the heating of Si to 1000C, the oxygen atoms become regrouped Si ₂ O → SiO ₂ + Si The electrically neutral groups of SiO ₂ interact with the phosphorus	
perties are conditioned by the presence of oxygen in silicon in the form of monodisperse Si ₂ O groups. In the process of the heating of Si to 1000C the oxygen atoms become regrouped Si ₂ O → SiO ₂ + Si The electrically neutral groups of SiO ₂ interact with the phosphorus	-
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$5910_{-} + 4p + 2p_{-0} + 581$	
701.45	
The resulting oxides of the impurity react with 8102	'4 7*
$xP_2O_5 + y81O_2 \rightarrow P_x81_yO_2$	1.
As a result, the P and O atoms are bound into electrically neutral: PxSiyO2 groups and the	
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. 2551-66 CCESSION NR: AP5021083		*	· 12	2	
llica glasses, the oxides berated oxygen diffuses to be crystal, is distributed catment leads to the form coups. These complexes me	ses. On heating to 1300c of the impurity, and the through the interstices and in the form of Si ₂ O grown nation of electrically act by be singly or multiply in	silicon di nd, followi ups. By co tive 8104 c ionized, th	ules of phospoxides decay, ng rapid coontrast, low-tomplexes/from us leading to	, and the ling of temperatur n Si ₂ O o an in-	6
rease in free-electron contributable to the decrease onged annealing. Orig. are SSOCIATION: Institut fizitibirsk (Institute of Semications)	se in the number of therms rt. has: 3 figures. Iki poluprovodnikov Sibirs conductor Physics, Siberis	al defects skogo otdel an Departme	in the proces eniya AN SSSI nt, AN SSSR)	ss of pro- [16]	教養を表する。 ときない (場合) マイン
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L 14562-66 EVT(m)/EWP(w)/T/EWP(t)/EMP(b) IJP(o) JD

ACC NR. APG002015 (A) SOURCE CODE: UR/0288/65/000/003/0079/0085

AUTHOR: Kravchenko, A.F.; Kornilovich, A.A.; Saks, L.A.; Sirotkina, V.P.

ORG: Institute of Semiconductor Physics, Siberian Branch, AN SSSR, Novosibirsk (Institut) fiziki poluprovodnikov Sibirskogo otdeleniya AN SSSR)

TITLE: Electrical properties of silicon with phosphorus admixtures .

SOURCE: AN SSSR. Sibirskoye otdeleniye. Izvestiya. Seriya tekhnicheskikh nauk, no. 3, 1965, 79-85

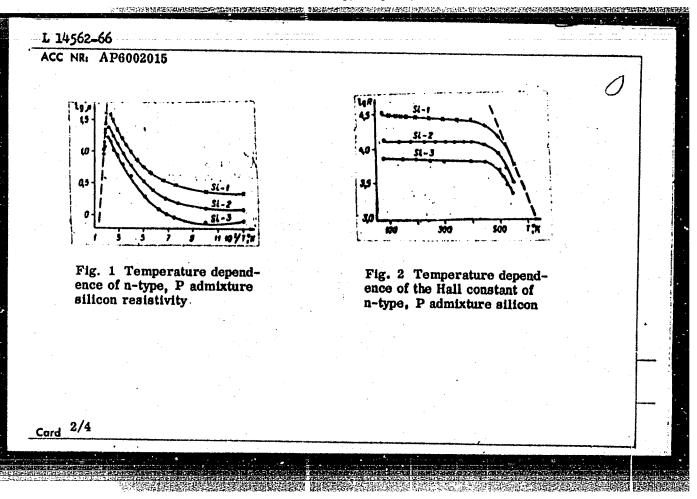
TOPIC TAGS: silicon semiconductor, specific resistance, Hall effect, thermoelectromotive force, phonon scattering

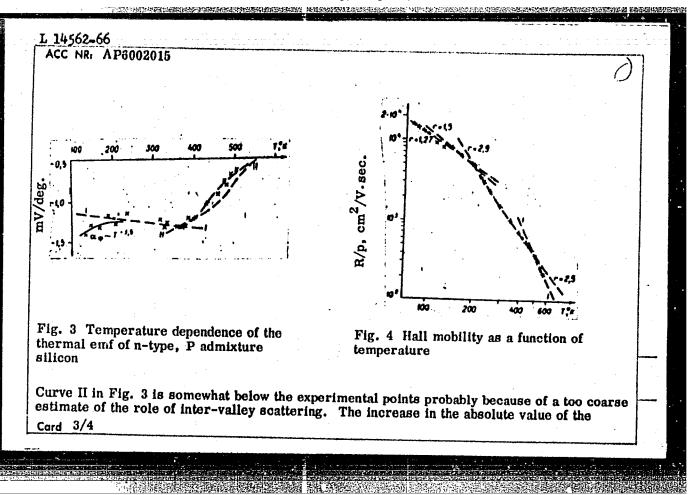
ABSTRACT: The majority of darlier works concerning the influence of phosphorus on the physical properties of silicon were carried out on polycrystalline materials in which the intercryatalline potential barriers made the interpretation of kinetic effects extremely complicated. In view of the present-day uses of n-type silicons with low P content, the authors investigated effects in three types of Si samples (Si-1, Si-2, Si-3) with differing P concentration having at room temperature specific resistivities of 18, 9, and 6 ohm cm. Experimental results are summarized in Figures 1 through 4. A detailed theoretical interpretation of the experimental results is also given. The theoretical dashed curves in Fig. 4 are in good agreement with experimental data except in the low temperature region, where the deviation may be due to admixture scattering which was neglected during the theoretical derivation.

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539.295:537





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1. (1774-1-17 vot(n)/s.ar(t)/srg Idir(c) ab/Jo WCC NY Alwa 5615 SOURCE CODE: UR/0139/66/000/003/0074/0079 AUTHOR: Kravehenko, A. F. ORG: Institute of Physics of Semiconductors, SO AN SSSR (Institut fiziki poluprovod-TITLE: Galvanomagnetic and thermomagnetic phenomena in compensated gallium arsenide SCURCE: IVUZ. Fizika, no. 3, 1966, 74-79 TOPIC TAGS: gallium arsenide, galvanomagnetic effect, thermomagnetic effect, Hall effect, magnetoresistance, Nernst effect, Ettingshausen effect, electron density, electron mobility, electron scattering ADSTRACT: The author measured, in a wide range of temperatures, several kinetic characteristics of gallium arsenide (Hall effect, magnetoresistance, Nernst-Ettingshausen effect) in which the free-electron density at room temperature did not exceed 1015. em-3. The purpose of the investigation was to determine the dominating mechanism of scattering and to explain the previously observed disparity between the electron mobility and the electron density. Standard procedures were used for the measurements. The results show that at low temperatures the electrons are scattered predominantly from the impurity atoms and from the optical vibrations, while at high temperatures the scattering is by acoustic phonons. In the presence of simultaneous scattering by thermal vibrations and by impurity ions, the principal role in the longitudinal Nernst Ettingshausen effect at T > 300K is played by the scattering by acoustic phonons. Card

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ACC NR: ARGO23415

Whereas the transverse Nornst-Ettingshausen effect reverses sign near 285%, the longitudinal one does not. The mobility calculated from the dependence of the magnetoresistance on the magnetic field intensity does not agree with the value of the mobility measured from the Hall effect. The discrepancy is attributed to a possible anisotropy of the scattering. Orig. art. has: 3 figures and 4 formulas.

SUB CODE: 20/ SUBM DATE: 3laug64/ ORIG REF: 006/ OTH REF: 014

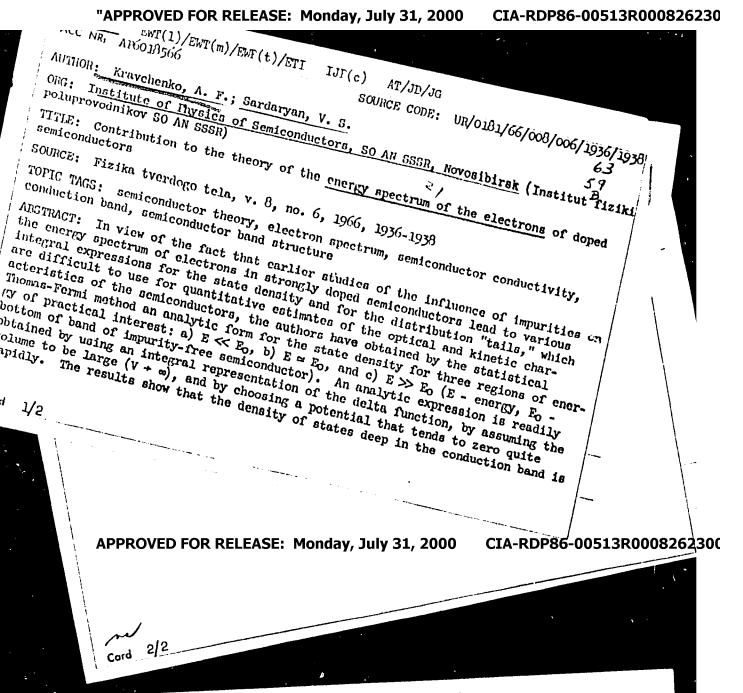
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CIA-RDP86-00513R000826230

L 38890-66 EWT(1) IJP(c)
ACC NR: AP6018557 SOURCE CODE: UR/0181/66/008/006/1899/1902
AUTHOR: Kravchenko, A. F.; Sardaryan, V. S.; Magarill, L. I.
ORG: Institute of Physics of Semiconductors, SO AN SSSR, Novosibirsk (Institut fiziki
poluprovodníkov SO AN SSSR)
TITLE: On the phenomenological theory of the longitudinal Hall effect
SOURCE: Fizika tverdogo tela, v. 8, no. 6, 1966, 1899-1902
TOPIC TAGS: Hall effect, cubic crystal, semiconductor conductivity
AESTRACT: A phenomenological theory is developed for the longitudinal Hall effect in cubic crystals in the case of anisotropic relaxation time and two-band conductivity, and anisotropic dispersion. Expressions are derived for the different components of the conductivity corresponding to both spherical and anisotropic minima, neglecting intervalley transitions. Formulas are then presented for the coefficients of the generalized conductivity tensor in terms of experimentally measured quantities. In the latter case expressions are given for both the longitudinal and planar Hall effects. The results show that the longitudinal Hall field does not act on the spherical minimum, whereas the planar and ordinary Hall fields are expressed in terms of kinetic parameters of both bands, and that experimental investigation of the longitudinal Hall effect yields important information on the anisotropy of the additional minima. The authors thank V. L. Pokrovskiy for valuable remarks. Orig. art. has: 23 formulas.
SUB CODE: 20/ SUBM DATE: 02Aug65/ ORIG REF: 004/ OTH REF: 004
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JD/JG EWT(1)/EWT(m)/EWP(t)/ETI/EWP(k) IJP(c) SOURCE CODE: UR/0046/66/012/003/0369/0372 . 06230-67 ACC NRI AP6029535 AUTHOR: Bobylev, B. A.; Kravchenko, A. F.

ORG: Institute of the Physics of Semiconductors, SO AN SSSR, Novosibirsk (Institut fiziki poluprovodníkov, SO AN SSSR)

TITLE: Absorption of ultrasonic waves in junctions of GaAs and GaSb 27

SOURCE: Akusticheskiy zhurnal, v. 12, no. 3, 1966, 369-372

TOPIC TAGS: ultrasonic wave, phonon interaction, ultrasound absorption

ABSTRACT: This paper presents experimental measurements of the damping of ultrasonic waves in semiconductor junctions of GaAs and GaSb. The frequency dependence of this absorption is examined in the range 20-200 megacycles; the temperature dependence is observed over the interval T = 95 K to T = 300 K. The measurements were made using the "pulse technique" in which radiofrequency pulses, each lasting a few microseconds, generate sound waves which reflect back and forth between the parallel faces of a crystal specimen of the metal being studied. As the sound wave travels through the metal, it is gradually damped as a result of (at least) four distinct processes: 1) ordinary damping of longitudinal waves as they pass through an isotropic medium; 2) absorption due to the interaction of elastic waves with dislocations in the crystal structure; 3) thermoelastic absorption; and 4) absorption due to the interactions between phonons and electrons. The samples of GaAs and GaSb were oriented in the direc-

UDC: 534.286

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CC NR: AP6029535 cions <111>, <110>, and <112>, and both longitudinal and transverse waves we luced. The damping of the sound waves was found to be almost independent of ture, over the range of temperatures considered. However, the damping appearure, over the range of temperatures considered. However, the damping appearure, over the range of temperatures considered. However, the damping appearure, over the range of temperatures considered.	rs to be
strongly frequency-dependent. The absorption contains a frequency-dependent. The absorption contains a frequency-dependent. The absorption contains a frequency factor of the exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n , measured experimentally, was found to a follows: $\alpha \sim f^n$. The exponent n is a follows: $\alpha \sim f^n$. The exponent $\alpha \sim f^n$ is a follows: $\alpha \sim f^n$. The exponent $\alpha \sim f^n$. The exponent $\alpha \sim f^n$ is a follows: $\alpha \sim f^n$. The exponent $\alpha \sim f^n$ is a follows: $\alpha \sim f^n$.	o take
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nastrantskalenantaletanne treetalungereesisteer († 18. juli 20. ju IJP(c) JD/JG EWP(t)/ETI SOURCE CODE: GE/0030/66/017/002/0479/0488 L 08075-67 ACC NR AP6033896 AUTHOR: Kravchenko, A. F.; Sardaryan, V. S. ORG: Institute of Semiconductor Physics, Siberian Division, Academy of Sciences SSSR, Novosibirsk TITLE: The bottom structure of the conduction band in GaAs SOURCE: Physica status solidi, v. 17, no. 2, 1966, 479-488 TOPIC TAGS: magnetoresistance, Hall effect, gallium arsenide, semiconductor physics, semiconductor, semiconductor carrier, conduction band, semiconductor band structure ABSTRACT: The magnetoresistance and Hall effect were studied for oriented specimens of n-type gallium arsenide with carrier concentrations of 5 x 1015 to 1 x 10¹⁸cm⁻³ at temperatures of 78 to 800K. Almost all samples showed anisotropy of the transverse magnetoresistance and nonvanishing longitudinal magnetoresistance. The energy position of the minima and effective mass were estimated from the temperature dependence of the Hall coefficient [AW = 0.12] Card 1/2

ACC NR. AP6033896 0.36 eV, m; = 1.2 m, m; = 1.86 m, m1 = 0.37 m, . A model for the band structure in the vicinity of the conduction band edge was discussed, and was shown to be consistant with experimental data when anisotropy of electron scattering by weak oriented dipoles was taken into account. The authors thanked E. V. Skubnevskii for his assistance in measurements. Orig. art. has: 8 figures, 4 tables, and 13 formulas [Based on authors' abstract] SUB CODE: 20/ SUBM DATE: 30Mar66/ ORIG REF: 012/ OTH REF: 009/ r

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ACC NR: AP6026304

SOURCE CODE: UR/0288/66/000/001/0078/0086

AUTHOR: Kravchenko, A. F.; Sardaryan, V. S.

ORG: Institute of Semiconductor Physics, Siberian Department, AN SSSR, Novosibirsk (Institut fiziki poluprovodnikov Sibirskogo Oodeleniya AN SSSR)

TITLE: Influence of impurities on the electron energy spectrum in semiconductors

SOURCE: AN SSSR. Sibirskoye otdeleniye. Izvestiya. Seriya tekhnicheskikh nauk,

TOPIC TAGS: electron energy spectrum, semiconductor impurity, electron energy level

ABSTRACT: An analytical expression is derived for the density of electron states in a semiconductor, for energy levels of practical interest, in a form convenient for numerical computation. The analysis is developed for a semiconductor containing (of a single type) distributed uniformly over the crystal. The presence of randomly distributed charged particles gives rise in a semiconductor to an additional electrostatic potential that varies from point to point. The field of the charged impurities characterized by a screening potential proportional to the potential electron

$$v_{i,j}(r) = v(r_i - r_j) = -\frac{e^2}{e(|e_i - r_j|)} e^{-\frac{|r_i - r_j|}{r_e}},$$
 (3)

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VDC: 621.315.592

ACC NR. AP6026304

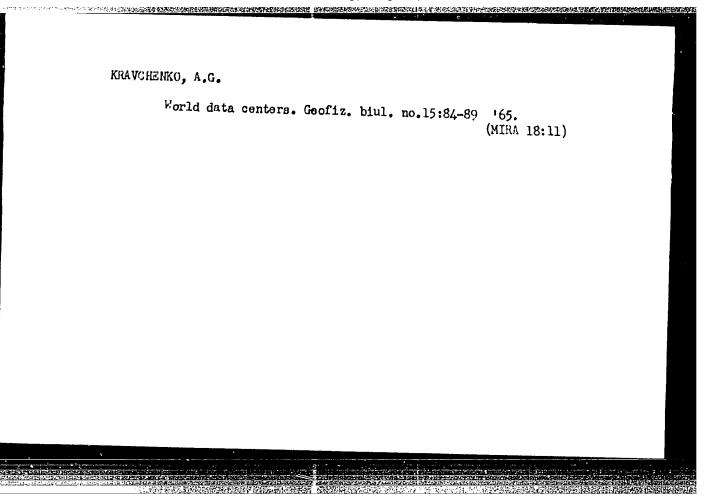
where is the dielectric constant of the semiconductor, and i and j are the electron and impurity numbers, respectively. Based on this model representation, and using the Thomas-Fermi statistical method, the expression for the density of the electron states in the conduction band is obtained in the form

$$\rho(E) = Q \int_{-\infty}^{E} \frac{(E - I)^{1/2} e^{-PI}}{(\alpha + \beta I + \gamma I)^{1/2}} dt.$$
 (20).

An evaluation of this integral for various electron energies leads to a relation between the density of the electron states in the conduction band and the total electron energy. The specific calculations involved in the analysis are given in appendices. The authors are indebted to I. M. Tsidil'kovskiy, V. V. Serebriakov, N. Ye. Tovmasian, and E. M. Skok for valuable discussions. Orig. art. has: 51 formulas and 1 figure.

SUB CODE: 20/ SUBM DATE: 10Jun65/ ORIG REF: 007/ OTH REF: 008

Card 2/2



OLIGICAL PROGRAMMENTALIA PROGRAMMENTA PROGRAMENTA PROGRAMENTA PROGRAMENTA PROGRAMENTA PROGRAMENTA PROGRAMENTA PROGRAMENTA PROGRAMENTA PROGRAME KKAVCHENKO, A.L. BARTAK, G.Ye.; KRAVOHENKO, A.G. Effect of medinal on exchange of sugar between blood and cerebral cortex. Vop. fiziol. no.7:115-124 154. (MLRA 8:1) 1. Dnepropetrovskiy meditsinskiy institut. (BARBITURATES, effects, barbital sodium on sugar exchange between blood & cerebral cortex) (HEMATOENCEPHALIC BARRIER. eff. of barbital sodium on sugar exchange between blood & cerebral cortex) (BLOOD SUGAR, eff. of harbital sodium on sugar exchange between blood & cerebral cortex) (CEREBRAL CORTEX, physiology, eff. of barbital sodium on sugar exchange between blood & cerebral cortex)

137-58-4-7207

Translation from: Referativnyy zhurnal, Metallurgiya, 1958, Nr 4, p 127 (USSR)

Fomichev, I. A., Vdovin, F. V., Kravchenko, A.G., Pishchik. AUTHORS:

N. S.

TITLE: Manufacture of Tubes From Austenitic lKhl4Nl4V2M (EI-257)

Steel [Proizvodstvo trub iz austenitnoy stali 1Kh14N14V2M

(EI-257)

PERIODICAL: Byul. nauchno-tekhn. inform. Vses. n.-i. trubnyy in-t, 1957, Nr 3, pp 5-16

ABSTRACT: Tubes of lKhl4Nl4V2M are designed for use for re-heaters

and manifolds of boilers operating under high and superhigh steam parameters. This steel (S) is a S of the austenitic class and is highly heat-resistant. The effects of temperature and degree of reduction on the plasticity of the S were investigated, and experiments were conducted in rolling the tubes on an automatic 400 mill. Forged hollow and solid blanks with machined surfaces were employed. Plasticity was determined by torsion testing, by testing

for pierceability, and for tension in a single plane (this last method was employed for the first time and makes it possible to determine

Card 1/2 the relationship between the temperature and plasticity, under

137-58-4-7207

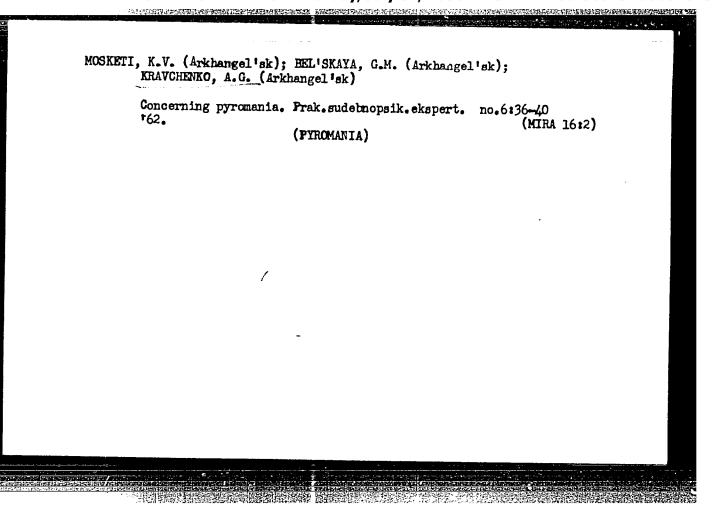
Manufacture of Tubes From Austenitic 1Kh14N14V2M (E1-257) Steel

conditions of stress similar to those of the real stresses existing during piercing, and, consequently, the optimum temperature for the working of the S). The design of the apparatus for testing for plane tension is appended and described. An analysis of the results of the torsion, plane tension, piercing, and microstructure tests is presented. This shows that piercing of the blank should best be performed in the 1200-1225°C temperature interval. The results of tests for pierceability and high-temperature torsion show that as the length of time the metal is held for purposes of heating increases the plasticity of the S drops. After obtaining the results of laboratory investigation, rolling of tubes of 219x 27 mm dimensions was performed successfully both from hollow and from solid blanks. Solid blanks are recommended as being economically advantageous.

1. Steel tubes--Manufacture 2. Steel tubes--Material

Card 2/2

Card 1/1		Pub. 124 - 16/39			
Authors 1	ŧ	Kravchenko, A. G.			
Title)	Documents on the nomination of N. K. Krupskaya as I Acad. of Sc., USSR	honorary member	of the	
Periodical :	ı	Vest. AN SSSR 26/2, 92-94, Feb 1956			;
Abstract :		Announcement is made by the Archives of the Academy the preservation of a special protocol dated February	y of Sc., USSR a	ifvine	
		that N. K. Krupskaya (widow of V. I. Lenin) was made of the Academy of Sciences, USSR for her great contidevelopment of the Communist ideology. Eleven USSR	de an honorary m tributions to th	ember e	21.0
Institution	•	of the Academy of Sciences, USSR for her great cont	de an honorary m tributions to th	ember e	
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ACCESSION NR: AR4018328

8/0137/64/000/001/D038/D038

SOURCE: RZh. Metallurgiya, Abs. 1D237

AUTHOR: Pishchikov, G. P.; Kravchenko, A. G.

TITLE: Making boiler pipe of PZ, 12Kh2MFSR, E1756, ET/13, E1695R, and EP17 steels

CITED SOURCE: Sb. Proiz-vo trub. Vy*p. 9.M., Mctallurgizdat, 1963, 13-18

TOPIC TAGS: pipe rolling, steel pipe, steel pipe manufacture, steel plasticity, steel puncture strength, rolling mill operation

TRANSLATION: Tests for warping were conducted on samples 90 and 250 mm in diameter at temperatures of 1,000-1,275 degrees every 50-25 degrees. The plasticity according to the amount of twists was tested to destruction, and the resistance to deformation was studied according to the intensity of twisting. It was determined that the plasticity of 12Kh2MFBR steel up to 1,270 degrees increases continuously (at 1,000 degrees, the number of twists is 22, at 1,250 degrees, 46), steel PZ changes little (at 1,000, the number of twists equals 20, at 1,100 degrees, 22, and at 1,250 degrees, 20). The intensity of twisting for all steel studied diminished proportionately with the increase in temperature. Thus, for three samples of

Card 1/2

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ACCESSION NR: AR4018328

12Kh2MFSR steel 250 mm in diameter, at 1,000 degrees, the intensity was zero; at 1,100 degrees, 6 kg, and at 1,250 degrees, 1.8 kg. In twisting samples of large diameters, the plasticity of the peripheral zones was higher than that of the central zones. For testing for puncture strength, conical samples were used, which made it possible to have a zone of pressing of 0-14.36. On the basis of the results of tests, schedules for hot rolling of boiler pipes were worked up. Then, pipes measuring 89 x 11 mm were rolled on an automatic "140" installation, and pipes measuring 152 x 25, 168 x 26, and 273 x 36 mm were rolled on an automatic "400" installation. Forged faced samples of solid cross-section were used for rolling. Experimental rolling took place normally. The external surface of the pipes was good. The pipes of PZ steel had minor defects 200 mm on their ends. Pipes of EI713, EP17, and EI695R has minor defects on their internal surfaces. Tables are given of the parameters of piercing and set up of the mill, and also the basic industrial parameters for the manufacture of pipes of the above-mentioned types of steel.

SUB CODE: MM, IE

ENCL: 00

Card 2/2

KRAVCHENKO, A.I.

Periodic fluctuations of the intragastric temperature and the periodic motor function of the empty stomach in true gastric achylia. Vrach.delo no.10:91-95 0 '62. (MIRA 15:10)

1. Fakul'tetskaya terapevticheskaya klinika (zav. - akademik V.N. Ivanov [demased]) Kiyevskogo meditsinskogo instituta.

(STOMACH-SECRETIONS) (PERIODICITY)

AUTHOR: Kravchenko, A.I. SOV/130-58-7-29/35

TITLE: According to Increased Obligations (Po povyshennym

obyazatel'stvam)

PERIODICAL: Metallurg, 1958, Nr 7, p 41 (USSR).

ABSTRACT: The author mentions that the personnel of Nr l melting shop at the imeni Andreyeva (imeni Andreyev) Works undertook, in honour of the "Day of the Metallurgist" to revise production plans upwards and that his crew (under Stalin prize-winner Zhukov) fulfilled the 1957 production plan to 102.7%, the corresponding figure for the first quarter of 1958 being 106%. He states that his crew are competing with the crew under I.I. Chursinov at the Pervoural'skiy novotrubnyy Works and that the enthusiasm of workers has risen since the introduction of the seven-hour day.

ASSOCIATION: Zavod imeni Andreyeva (imeni Andreyev Works)

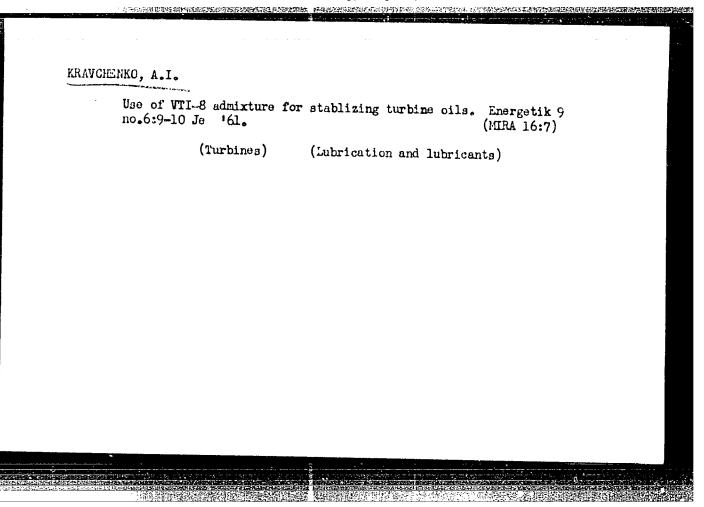
Card 1/1 1. Labor--Performance 2. Labor--USSR 3. Metals--Production

SLUTSKIY, S.S., kand.ekonom.nauk; PILIPCHUK, A.I., nauchnyy sotrudnik; ANTONOV, M.F., kand.tekhn.nauk; MALYARCHUK, G.S., kand.tekhn.nauk. Prinimali uchastiye: MEL'NIKOV, A.A., inzh.; ARSEN'YEVA, A.I., inzh.; TEREKHOVA, Z.S., tekhnik; SIDOROVA, L.N., tekhnik; ISSERLIS, I.I., tekhnik; KRAVCHENKO, A.I., inzh. POSTNIKOV, S.A., inzh., red.; ZHULIN, V.K., otv. za vypusk; POKHLEHKINA, N.I., tekhn.red.

[Efficient distribution of and organization of work at cargo transfer points] Ratsional noe resmeshenenie i organizatsiia raboty punktov perevalki. Pod obshchei red. S.S.Slutskogo. Moskva, 1960. 127 p. (HIRA 14:2)

1. Moscow. TSentral'nyy nauchno-issledovatel'skiy institut ekonomiki i ekspluntatsii vodnogo transporta. 2. TSentral'nyy nauchno-issledovatel'skiy institut ekonomiki i ekspluatatsii vodnogo transporta (for Slutskiy, Pilipchuk, Terekhova, Sidorova, Isserlis). 3. Institut komplekenykh transportnykh problem AN SSSR (for Antonov, Malyarchuk, Kravchenko).

(Cargo handling)



KRAVCHENKO, A.1.

Intracutaneous test by means of an autoserum in Botkin's disease. Vrach. delo no.11:86-90 N'63 (MIRA16:12)

1. Kafedra infektsionnykh bolezney Klysyckego meditsinskego instituta.

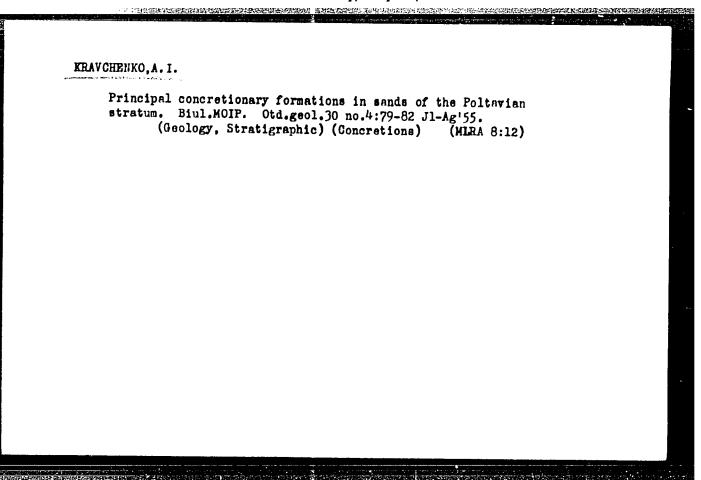
KRAVCHENKO, A.I.

Intragastric temperature in various diseases. Vrach. delo no.10:36-40 0 '63. (MIRA 17:2)

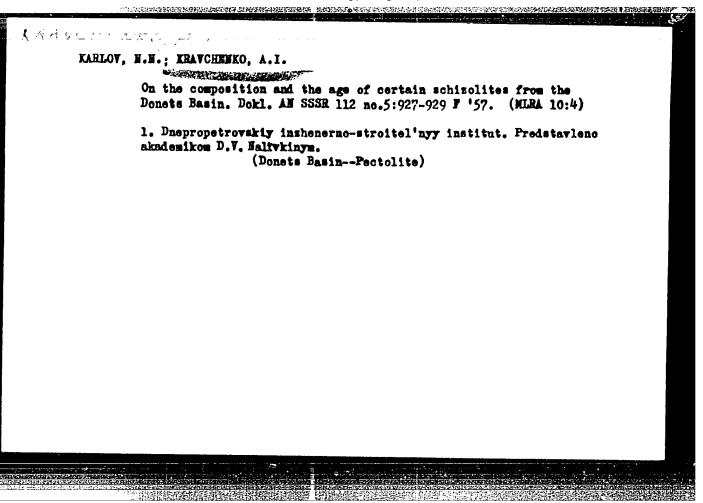
1. Fakulitetskaya terapevticheskaya klinika (zav. - prof. G.I. Burchinskiy) Kiyevskogo meditsinskogo instituta.

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

KRANCHENKO, A. I. USER/ Geology - Volcanic action Card 1/1 Pub. 86 - 1/37 Authors * Karlov, N. N., and Kravchenko, A. I. Title New deposits of volcanic ashes at Drepropetrovsk Priroda 44/4, 118 - 119, Apr 1955 Periodical Abstract A description is given of volcanic ash deposits at Dniepropetrovsk, which, it is believed, floated in the air for long distances before settling at this point. A study of this rather loose material of relatively recent volcanic action makes possible the determination of the time and intensity of volcanic eruptions in the quarternary and tertiary periods. Illustration; drawing. Institution: Submitted



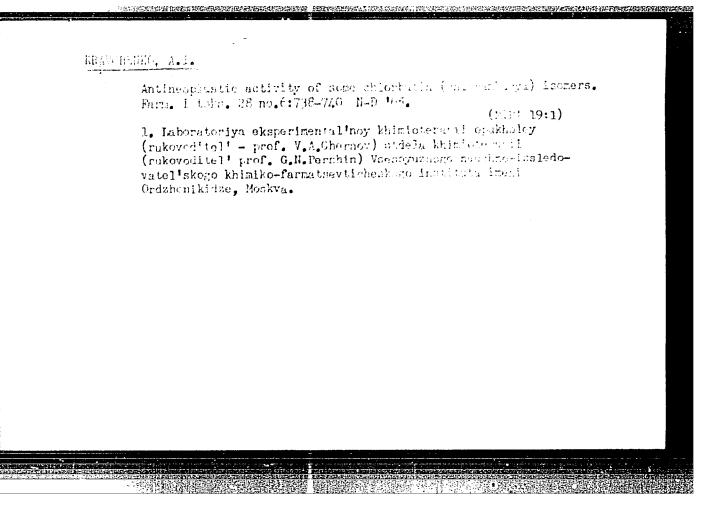
KRAVCHENKO, A.I. Composition and origin of the sand dunes of the Baltic Sea region. Izv. Vses. geog. ob-va 87 no. 1:68-70 Ja-F '55. (Baltic Sea region—Sand dunes)



KARLOV, N.N.; KRAVCHENKO, A.I.

Contribution of N.I. Dmitriev to the study of the geology of the Quaternary and the geomorphology of the Ukraine. Biul. Kom. chetv. per. no.24:138-144 60. (MIRA 16:7)

(Ukraine-Geology)



KRAVCHENKO, A.I. (Moskva, Novo-Gireyevo, 16/45, kv. 44)

Measuring the nucleus size of blastomeres and cells at initial stages of devolopment in Triton taeniatus L. Arkh. anat., gist. i embr. 47 no. 7:22-29 Jl * 64.

1. Inboratoriya eksperimental noy khimioterapii opakholey (rukovoditel - doktor med. nauk V.A. Chernov) Vsesoyuznogo nauchno-issledovatel skogo khimiko-farmatsevticheskogo instituta imeni Ordzhonikidze, Moskva. Suhmitted April 4, 1963.

GRIGOR'YEV, Te.T., inshener; KRAVCHENKO, A.I., inzhener.

Utilizing trailing weight of type 2-2 electric locomotives. Vest.
TSNII MFS 15 no.2:22-25 S '56. (MIRA 9:12)

1. Novocherkasskiy elektrovozostroitel'nyy zavod imeni S.M. Budennogo.

(Bleptric locomotives)

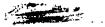
GRIGOR'YEV, Ye.T., inzh. KRAVCHENKO, A.I., inzh.

Using the adhesien weight of electric lecomotives with oblique traction. Vest. TSNII MPS 17 no.8223-27 D '58. (MIRA 12:1)

1.Novecherkasskiy elektrovezostreitel'nyy zaved. (Electric lecomotives)

GRIGOR'YEV, Ye.T., inzh.; KRAVCHENKO, A.I., inzh.; NESTEROV, S.D., inzh.

Transverse elastic truck couplers for electric locomotives. Vest.
TSNII MPS 18 no.8:21-25 D 159. (MIRA 13:9)
(Electric locomotives)



KRAVCHENKO, A41., inzh.

Locomotives with a total utilization of the weight on the driving axles. Izv. vys. ucheb. zav.; mashinostr. no.3:129-234 60. (MIRA 14:3)

1. Moskovskoye vyssheye tekhnicheskoye uchilishche imeni Baumana. (Locomotives-Dynamics)

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

KRAVCHENKO, Aleksandr Ignatiyevich

Study of some structural factors of the M60 electric locomotive. Izv. vys. ucheb. zav.; elektromekh. 3 no.3:144-157 '60.

(MIRA 13:10)

1. Nachal'nik laboratorii perspektivnykh razrabotok Novocherkasskogo nauchno-issledovatel'skogo instituta elektrovozostroyeniya.
(Electric locomotives)

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0008262300

KRAVCHENKO, Aleksandr Ignat'yovich, inzh.

Traction displacements in the carriage of an electric locomotive. Izv. vys. ucheb. zav.; elektromekh. 3 no.6:112-118 '60. (MIRA 15:5)

l. Nachalinik laboratorii perspektivnykh razrabotok Novocher. kasskogo nauchno-issledovateliskogo instituta elektrovozostroyeniya. (Electric locomotives)

Investigating the horizontal static interaction of a locomotive and track on curves. Izv.vys.ucheb.zav.; mashinostr. no.?:142-148 '60.

(MIRA 13:11)

1. Novocherkasskiy elektrovemetroitel'nyy zavod.

(Locomotives—Performance)

THE SECTION OF THE PROPERTY OF

KRAVCHENKO, A.I.; SITNIK, N.Kh.

Ways of creating main-line electric locomotives on the basis of dimensional series and standardization. Sbor. nauch. trud. EINII 2:72-93 '62. (MIRA 16:8)

(Electric locomotives -- Design and construction)

IN COME TO BE AN ADDRESS OF THE PROPERTY OF TH

KRAYCHENKO, Aleksandr Ignat'yevich, inzh.; BRATOLYUBOV, Vsevolod, Borisovich, inzh.

Integral method for evaluating electric traction motors. Izv. vys.ucheb.zav.; elektromekh. 6 no.2:229-236 '63. (MIRA 16:4)

1. Nachal'nik laboratorii perspektivnykh razrabotok Novocherkasskogo nauchno-issledovatel'skogo instituta elektrovozostroyeniya (for Kravchenko). 2. Nachal'nik otdela Mordovskogo nauchno-issledovatel'skogo elektrotekhnicheskogo instituta (for Bratolyubov).

(Electric locomotives) (Electric railway motors)

DOROSHUK, G.P.; KRAVCHENKO, A.I.

Static problems concerning the motion of a 2-2-2 electric locomotive in curves and their calculation using the "Ural-1" digital computer. Sbor. nauch. trud. ElNII 3:171-191 '63.

(MIRA 17:4)

DOROSHUK, Georgiy Panteleyevich, mladshiy nauchnyy sourudnik; KRAVCHENKO, Aleksandr Ignat'yevich, inzh.

Reliability of systems with given statistical characteristics of their quality and applications. Izv. vys. ucheb. zav.; elektromekh. 8 no.4:367-377 165.

1. Vsesoyuznyy nauchno-issledovatel'skiy i proyektno-konstrukterskiy institut elektrovozostroyeniya (for Doroshuk). 2. Nachal'nik laboratorii perspektivnykh razrabotok Vsesoyuznogo nauchno-issledovatel'skogo i proyektno-konstruktorskogo instituta elektrovozostroyeniya (for Kravchenko).

"APPROVED FOR RELEASE: Monday, July 31, 2000

CIA-RDP86-00513R000826230

KRAVCHENKO, Aleksandr Ignat'yevich, Inzh.; KHAVCHENKO, Marina Ignat'yevich, ordinator

Use of a digital computer in solving a problem on the cognition of a logical image described by discrete information. Izv. vys. ucheb. zav.; elektromekh. 8 no.4:472-473 '65. (MIRA 18:5)

1. Nachal'nik laboratorii perspektivnykh razrabotok Vsesoyuznogo nauchno-issledovatel'skogo i proyektno-konstruktorskogo instituta nauchno-issledovatel'skogo i proyektno-konstruktorskogo instituta elektrovozostroyeniya (for Kravchenko, A.I.). 2. Klinika nervnykh bolezney i neyrokhirurgii Rostovskogo meditsinskogo instituta (for Kravchenko, M.I.).